

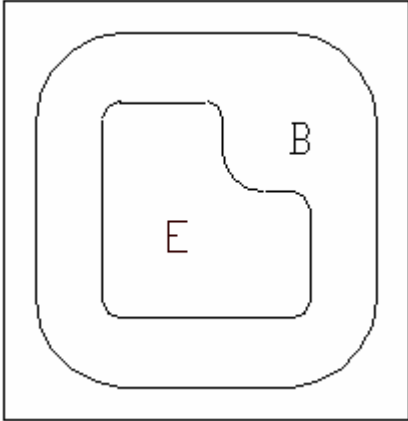
## BC856 Silicon PNP Epitaxial Transistor

Description :The BC856is designed for audio frequency general amplifier applications

Features: ●Excellent  $h_{FE}$  Linearity

●Complementary to BC846

## Chip Appearance

	Chip Size		350um × 350um
	Chip Thickness		210 ± 20um
	Bonding Pad Size	Base	110um × 110um
		Emitter	100um × 100um
	Front Metal		Al
	Backside Metal		Au
	Scribe line width		40um
	Wafer Size		6 inch

## Electrical Characteristics( Ta=25°C)

Characteristic	Symbol	Test Condition	Min	Max	Unit
Collector Cutoff Current	$I_{CBO}$	$V_{CB}=-30V, I_E=0$		-15	nA
Emitter Cutoff Current	$I_{EBO}$	$V_{EB}=-5V, I_C=0$		-0.1	uA
Collector-Base Breakdown Voltage	$BV_{CBO}$	$I_C=-0.1mA,$	-80		V
Collector-Emitter Breakdown Voltage	$BV_{CEO}$	$I_C=-1mA,$	-65		V
Emitter-Base Breakdown Voltage	$BV_{EBO}$	$I_E=-0.1mA,$	-5.0		V
DC Current Gain	$h_{FE}$	$V_{CE}=-5V, I_C=-2mA$	150	600	
Collector Saturation Voltage	$V_{CE(sat)}$	$I_C=-10mA, I_B=-0.5mA$		-0.3	V